RB161L-40

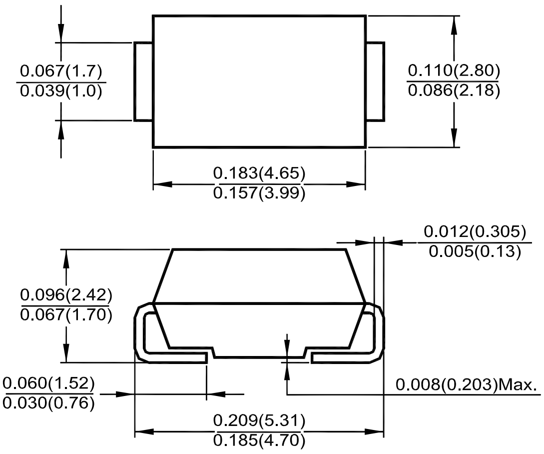
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

FOR HIGH FREQUENCY RECTIFICATION
AND SWITCHING POWER SUPPLY

Features

- Compact power mold type
- Ultra low V_F
- V_{RM} = 40 V guaranteed

SMA (DO-214AC)



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, resistive or inductive load, For capacitive load, derate by 20%

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Blocking Voltage	V_R	20	V
Mean Rectifying Current [1)]	I_O	1	A
Peak Forward Surge Current	I_{FSM}	70	A
Maximum Forward Voltage at I_F = 1 A	V_F	0.4	V
Maximum Reverse Current at V_R = 20V	I_R	1	mA
Operating Junction Temperature Range	T_J	125	°C
Storage Temperature Range	T_{Stg}	- 40 to + 125	°C

[1)] When mounting on PCB

Dated : 14/04/2008

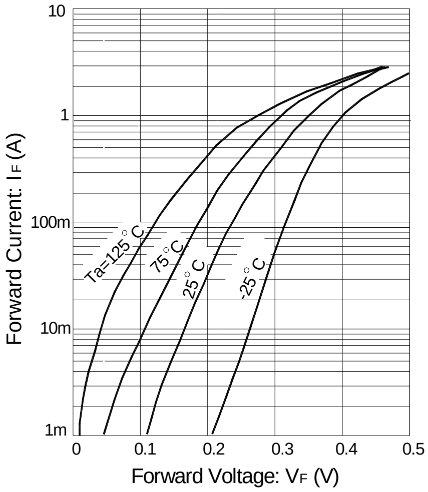


Fig. 1 Forward Characteristics

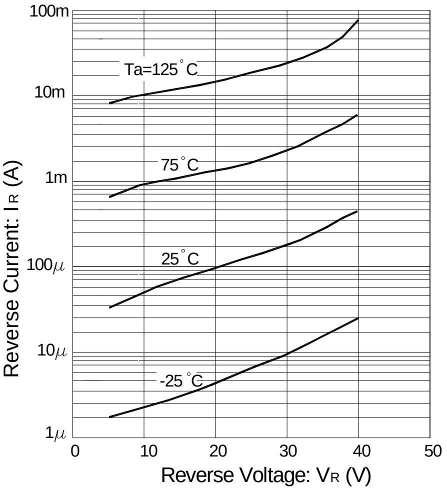


Fig. 2 Reverse Characteristics

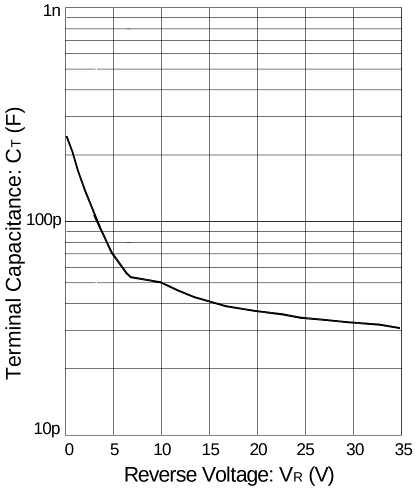


Fig. 3 Capacitance Between Terminals Characteristics

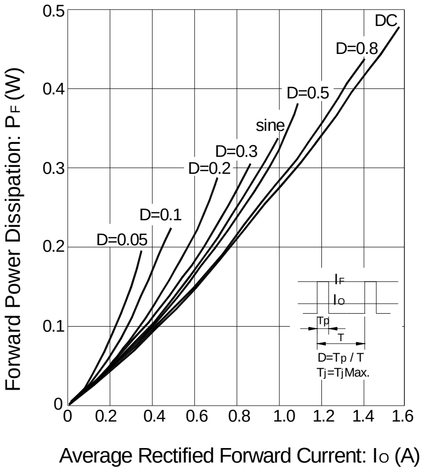


Fig. 4 Forward Power Dissipation Characteristics

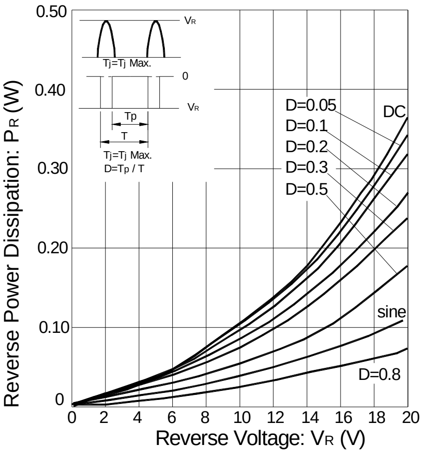


Fig. 5 Reverse Power Dissipation Characteristics

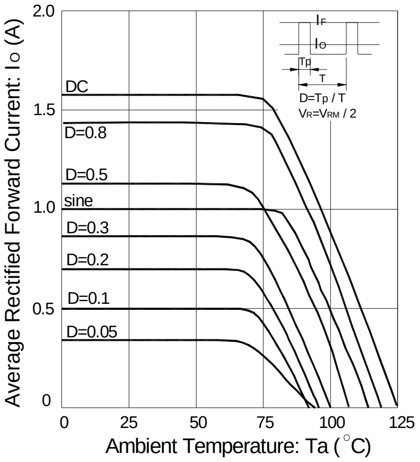


Fig. 6 Derating Curve (When Mounting On Glass Epoxy PCBs)

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